

ABSTRACT OF THE DISCLOSURE

A cleaning method for a CVD apparatus which forms films on wafers by introducing film forming gas into a chamber by means of a shower head. In this method, the NF_3 gas, which forms the cleaning gas including a compound containing fluorine atoms, is activated by exposure to microwaves by a microwave generating source, and then introduced into the chamber. The temperature of the lid section is raised by heating the lid section by means of a heater plate, or halting supply of cooling water to the lid section from the water supply source, whereby the temperature of the shower head during cleaning is raised above the temperature at which film formation onto the wafer is performed.